

# Automotive P-Channel 20 V (D-S) 175 °C MOSFET

### DESCRIPTION

The attached SPICE model describes the typical electrical characteristics of the p-channel vertical DMOS. The sub-circuit model is extracted and optimized over the -55 °C to +125 °C temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

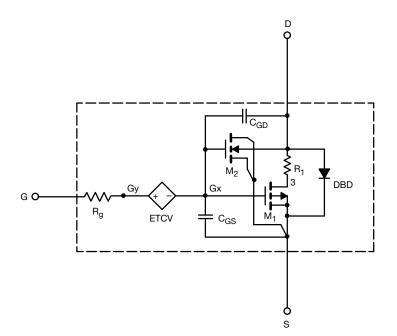
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A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched  $C_{gd}$  model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

### **CHARACTERISTICS**

- P-channel vertical DMOS
- Macro model (subcircuit model)
- Level 3 MOS
- · Apply for both linear and switching application
- Accurate over the -55 °C to +125 °C temperature range
- Model the gate charge

## SUBCIRCUIT MODEL SCHEMATIC



#### Note

• This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits



SPICE Device Model SQ3425EV

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<b>SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	TEST CONDITIONS	SIMULATED DATA	MEASURED DATA	UNIT
Static					
Gate threshold voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = -250 \ \mu A$	1.1	-	V
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = -4.5 \text{ V}, \text{ I}_{D} = -4.7 \text{ A}$	0.049	0.049	Ω
		$V_{GS} = -2.5 \text{ V}, \text{ I}_{D} = -1 \text{ A}$	0.010	0.089	
Forward transconductance <sup>a</sup>	9 <sub>fs</sub>	$V_{DS} = -10 \text{ V}, \text{ I}_{D} = -4.7 \text{ A}$	9.6	9	S
Diode forward voltage	V <sub>SD</sub>	I <sub>S</sub> = -1.7 A	-0.8	-0.8	V
Dynamic <sup>b</sup>					
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	595	560	pF
Output capacitance	Coss		184	178	
Reverse transfer capacitance	C <sub>rss</sub>		133	126	
Total gate charge	Qg	$V_{DS}$ = -10 V, $V_{GS}$ = -4.5 V, $I_D$ = -4.7 A	6.7	6.9	nC
Gate-source charge	Q <sub>gs</sub>		1.2	1.2	
Gate-drain charge	Q <sub>gd</sub>		2.6	2.6	

Notes

a. Pulse test; pulse width  $\leq$  300  $\mu s,$  duty cycle  $\leq$  2 %

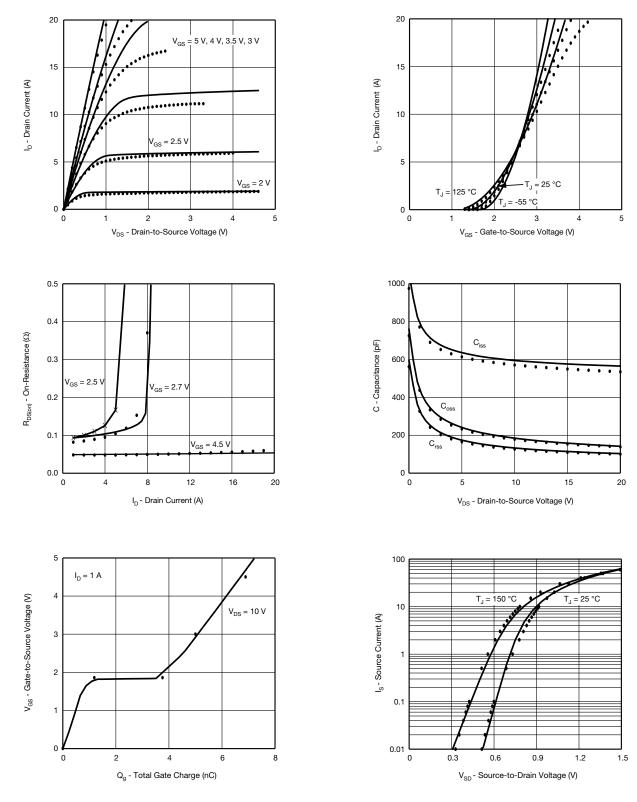
b. Guaranteed by design, not subject to production testing

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## COMPARISON OF MODEL WITH MEASURED DATA (T\_J = 25 °C, unless otherwise noted)



#### Note

• Dots and squares represent measured data Copyright: Vishay Intertechnology, Inc.

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